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NTD3813N

Power MOSFET

16 V, 51 A, Single N-Channel, DPAK/IPAK

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- Three Package Variations for Design Flexibility
- These are Pb-Free Devices

Applications

- DC-DC Converters
- High Side Switching

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit		
Drain-to-Source Voltage	V_{DSS}	16	V		
Gate-to-Source Voltage	V_{GS}	± 16	V		
Continuous Drain Current $R_{\theta JA}$ (Note 1)	I_D	$T_A = 25^\circ\text{C}$	13.8		
		$T_A = 85^\circ\text{C}$	10.7		
Power Dissipation $R_{\theta JA}$ (Note 1)	P_D	2.6	W		
Continuous Drain Current $R_{\theta JA}$ (Note 2)	I_D	$T_A = 25^\circ\text{C}$	9.6		
		$T_A = 85^\circ\text{C}$	7.4		
Power Dissipation $R_{\theta JA}$ (Note 2)	P_D	1.2	W		
Continuous Drain Current $R_{\theta JC}$ (Note 1)	I_D	$T_C = 25^\circ\text{C}$	51		
		$T_C = 85^\circ\text{C}$	39		
Power Dissipation $R_{\theta JC}$ (Note 1)	P_D	34.9	W		
Pulsed Drain Current	$t_p = 10\mu\text{s}$	$T_A = 25^\circ\text{C}$	I_{DM}	114	A
Current Limited by Package	$T_A = 25^\circ\text{C}$	$I_{DmaxPkg}$	35	A	
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$		
Source Current (Body Diode)	I_S	29	A		
Drain to Source dV/dt	dV/dt	6	V/ns		
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_L = 10\text{ A}_{pk}$, $L = 0.3\text{ mH}$, $R_G = 25\ \Omega$)	EAS	15	mJ		
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$		

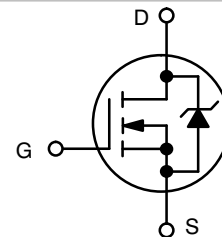
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



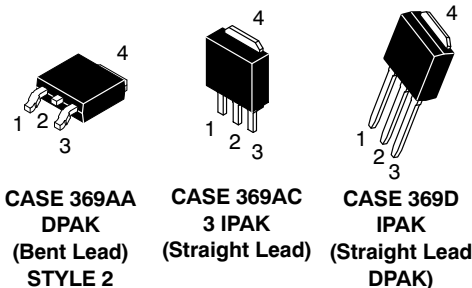
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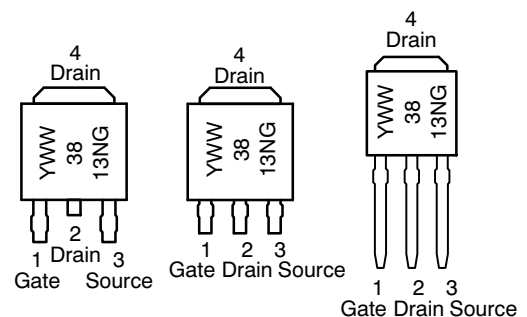
$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
16 V	8.75 m Ω @ 10 V	51 A
	14.5 m Ω @ 4.5 V	



N-CHANNEL MOSFET



MARKING DIAGRAMS & PIN ASSIGNMENTS



Y = Year
 WW = Work Week
 3813N = Device Code
 G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

NTD3813N

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	4.3	°C/W
Junction-to-TAB (Drain)	$R_{\theta JC-TAB}$	3.6	
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	58	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	121	

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	16			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			16.8		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 16\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.5		2.5	V	
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			5.3		mV/°C	
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 15\text{ A}$		7.2	8.75	m Ω
		$V_{GS} = 4.5\text{ V}$	$I_D = 15\text{ A}$		11	14.5	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}, I_D = 15\text{ A}$		40		S	

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 12\text{ V}$		963		pF
Output Capacitance	C_{OSS}			338		
Reverse Transfer Capacitance	C_{RSS}			191		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 12\text{ V}, I_D = 15\text{ A}$		8.5	12.8	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.93		
Gate-to-Source Charge	Q_{GS}			3.1		
Gate-to-Drain Charge	Q_{GD}			3.8		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 12\text{ V}, I_D = 15\text{ A}$		16.7		nC

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 12\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		12		ns
Rise Time	t_r			38		
Turn-Off Delay Time	$t_{d(OFF)}$			14		
Fall Time	t_f			5.0		
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 12\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		8.0		ns
Rise Time	t_r			33		
Turn-Off Delay Time	$t_{d(OFF)}$			20		
Fall Time	t_f			8.0		

3. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
4. Switching characteristics are independent of operating junction temperatures.
5. Assume standoff of 110 mm.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 15\text{ A}$	$T_J = 25^\circ\text{C}$	0.88	1.2	V
			$T_J = 125^\circ\text{C}$	0.76		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 15\text{ A}$		14.4		ns
Charge Time	t_a			6.8		
Discharge Time	t_b			7.6		
Reverse Recovery Charge	Q_{RR}			3.7		

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_A = 25^\circ\text{C}$		2.49		nH
Drain Inductance, DPAK	L_D			0.0164		
Drain Inductance, IPAK (Note 5)	L_D			1.88		
Gate Inductance	L_G			3.46		
Gate Resistance	R_G			0.4		

3. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
4. Switching characteristics are independent of operating junction temperatures.
5. Assume standoff of 110 mm.

NTD3813N

TYPICAL PERFORMANCE CURVES

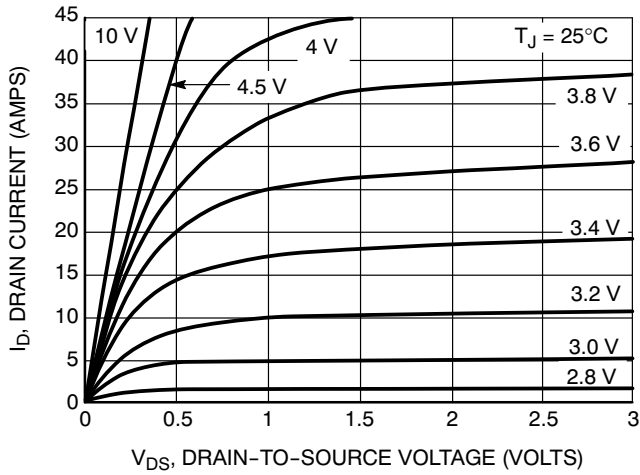


Figure 1. On-Region Characteristics

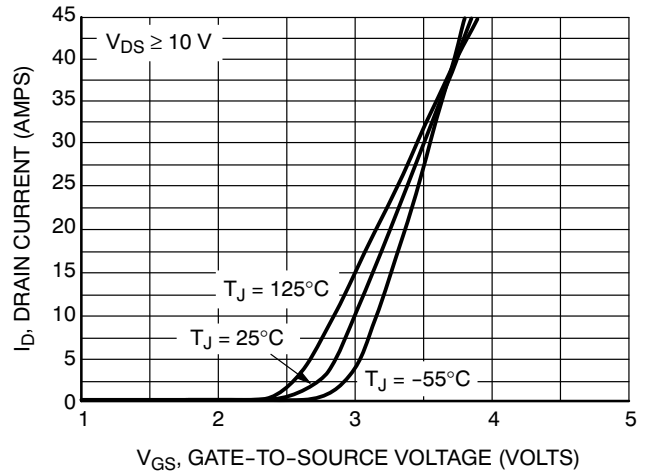


Figure 2. Transfer Characteristics

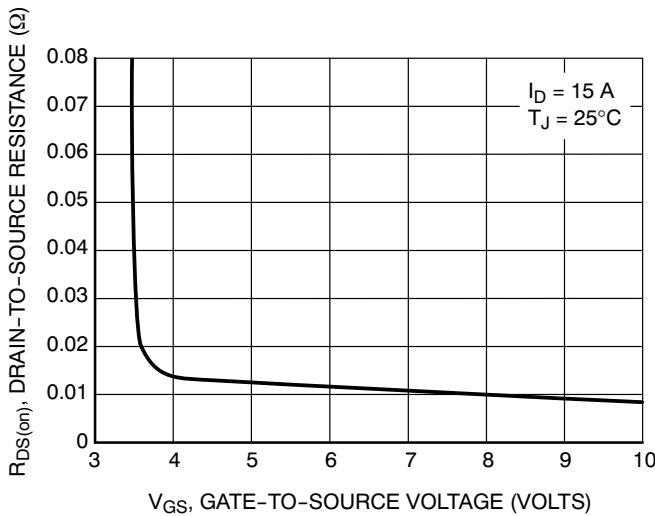


Figure 3. On-Resistance vs. Gate-to-Source Voltage

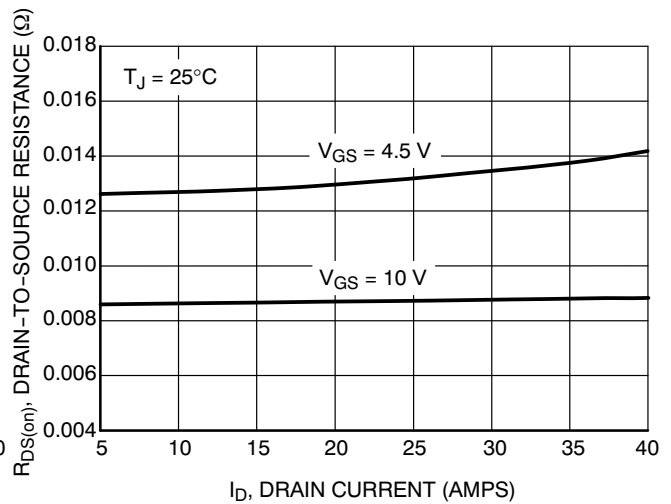


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

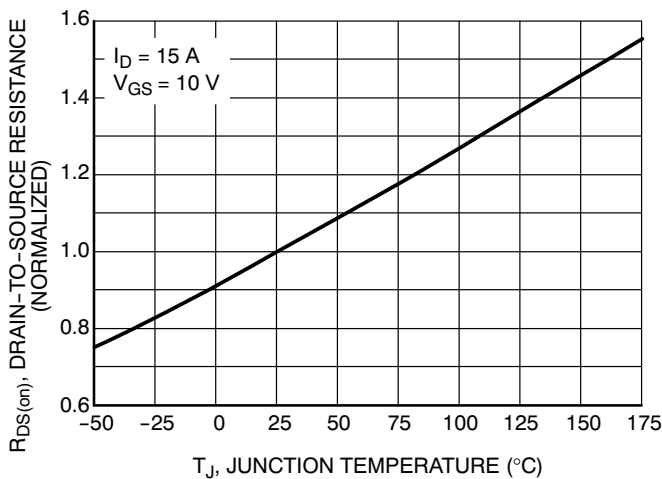


Figure 5. On-Resistance Variation with Temperature

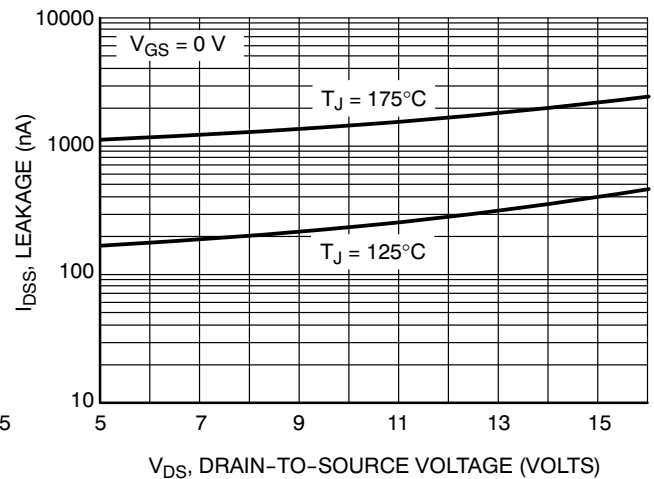


Figure 6. Drain-to-Source Leakage Current vs. Drain Voltage

TYPICAL PERFORMANCE CURVES

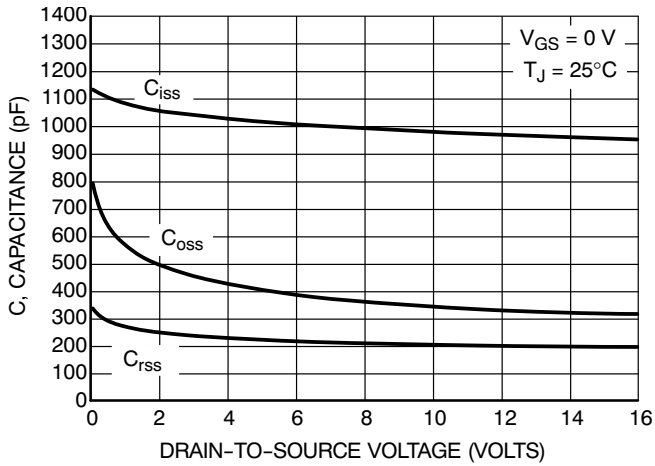


Figure 7. Capacitance Variation

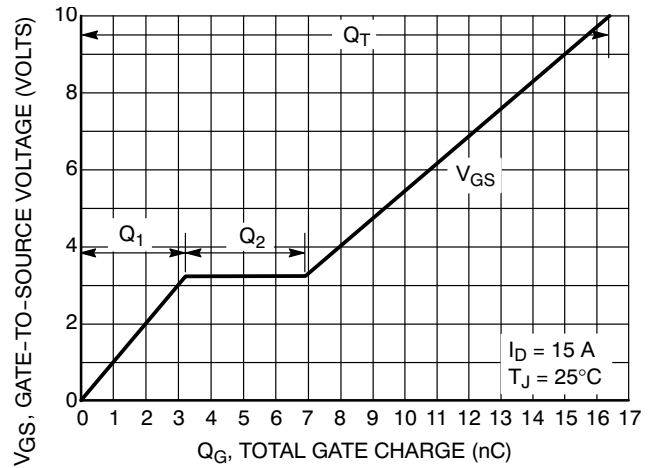


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

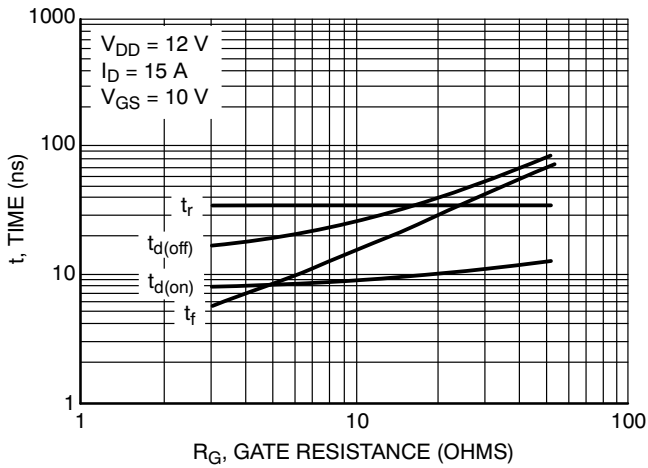


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

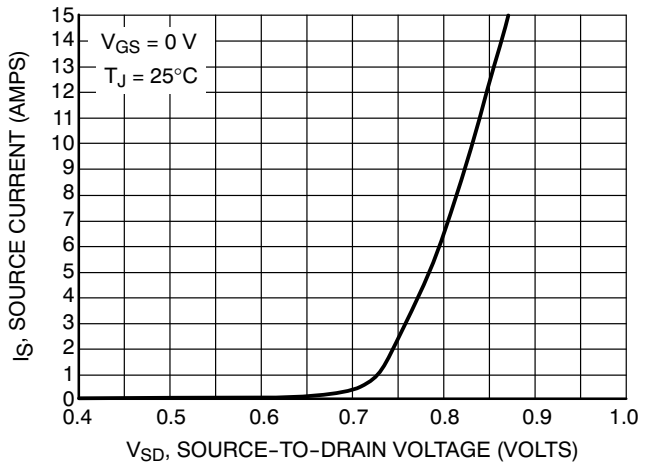


Figure 10. Diode Forward Voltage vs. Current

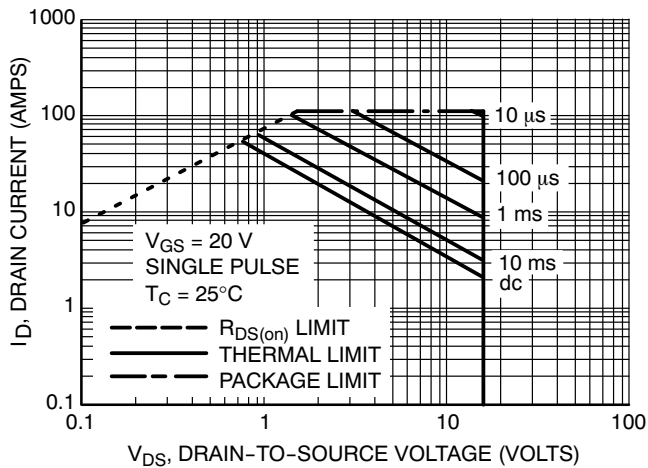


Figure 11. Maximum Rated Forward Biased Safe Operating Area

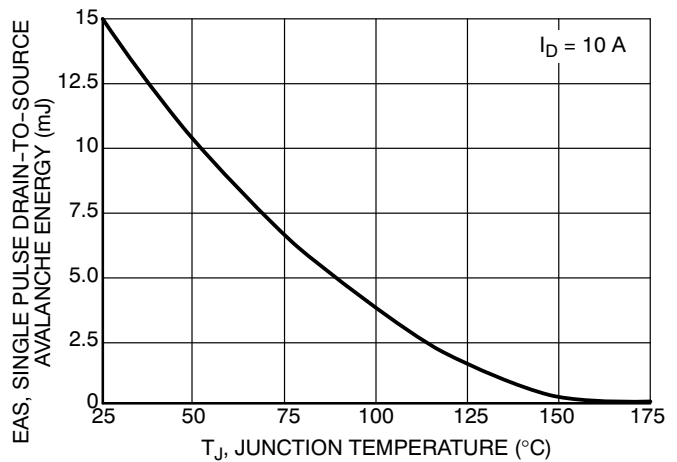


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

NTD3813N

ORDERING INFORMATION

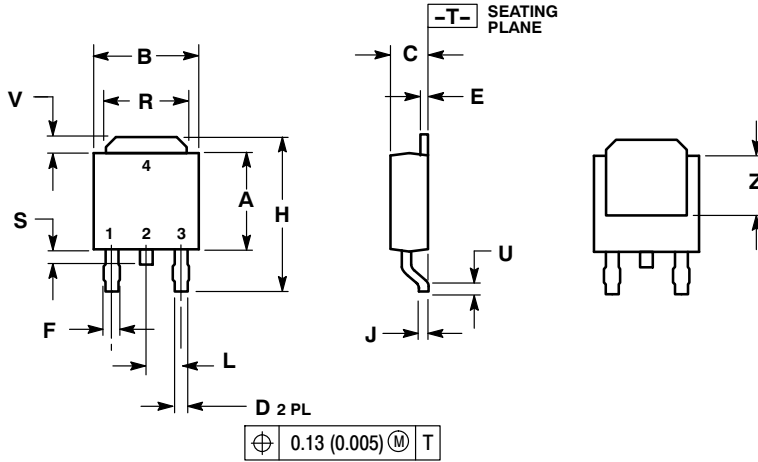
Device	Package	Shipping†
NTD3813NT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NTD3813N-1G	IPAK (Pb-Free)	75 Units / Rail
NTD3813N-35G	IPAK Trimmed Lead (3.5 ± 0.15 mm) (Pb-Free)	75 Units / Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTD3813N

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE)
CASE 369AA-01
ISSUE A

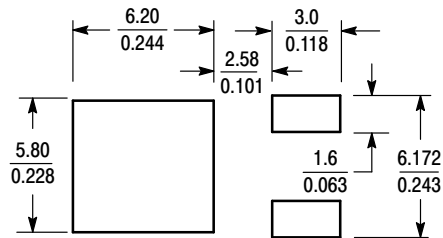


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.025	0.035	0.63	0.89
E	0.018	0.024	0.46	0.61
F	0.030	0.045	0.77	1.14
H	0.386	0.410	9.80	10.40
J	0.018	0.023	0.46	0.58
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.024	0.040	0.60	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



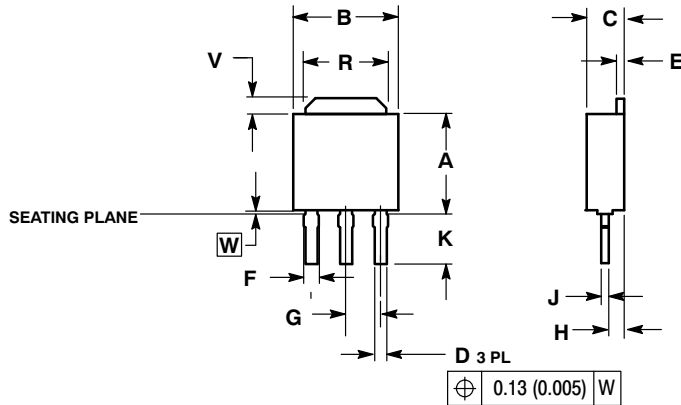
SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NTD3813N

PACKAGE DIMENSIONS

3 IPAK, STRAIGHT LEAD CASE 369AC-01 ISSUE O

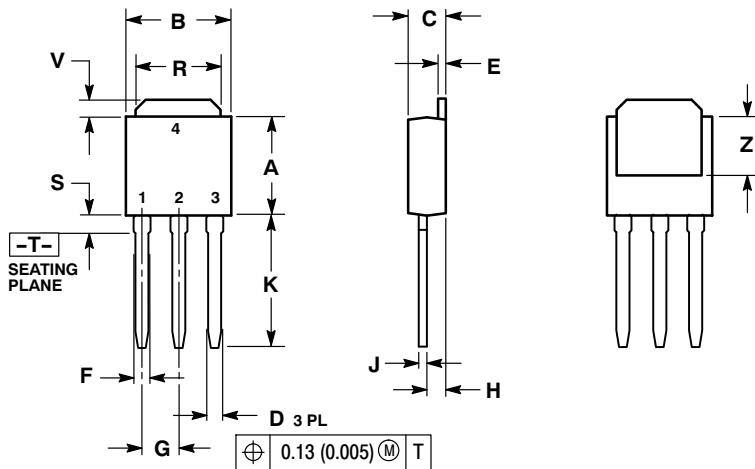


NOTES:

- 1.. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2.. CONTROLLING DIMENSION: INCH.
3. SEATING PLANE IS ON TOP OF DAMBAR POSITION.
4. DIMENSION A DOES NOT INCLUDE DAMBAR POSITION OR MOLD GATE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.043	0.94	1.09
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.134	0.142	3.40	3.60
R	0.180	0.215	4.57	5.46
V	0.035	0.050	0.89	1.27
W	0.000	0.010	0.000	0.25

IPAK (STRAIGHT LEAD DPAK) CASE 369D-01 ISSUE B



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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